

AMENDMENTS TO THE SPECIFICATION

Page 7, replace paragraph commencing at line 11 with the following amended paragraph:

In content of the layers 209a and 209b can be expressed as Equation (1) below.

$$2\% \text{ (1}^{\text{st}} \text{ InGaN layer)} \leq \text{In/InGa} \leq 3\% \text{ (2nd InGaN layer)} \quad (1)$$

$$\begin{array}{l} \text{In/InGa in 1}^{\text{st}} \text{ InGaN layer} \leq 2\%; \\ \text{In/InGa in 2}^{\text{nd}} \text{ InGaN layer} \leq 3\%; \text{ and} \\ \text{In/InGa in 1}^{\text{st}} \text{ InGaN layer} \leq \text{In/InGa in 2}^{\text{nd}} \text{ InGaN layer} \end{array} \quad (1)$$

Page 8, replace paragraph commencing at line 34 with the following amended paragraph:

It can be seen from Table 1 that the inventive light emitting device equipped with the InGaN/InGaN multi-layer 209 can normally operate even when an about-20-time higher ~~reverse~~ reverse voltage is applied thereto.